

2SA1194(K)

Silicon PNP Epitaxial

HITACHI

ADE-208-854 (Z)
1st. Edition
Sep. 2000

Application

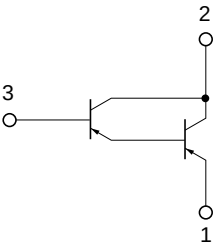
High gain amplifier

Outline

TO-126 MOD



- 1. Emitter
- 2. Collector
- 3. Base



Absolute Maximum Ratings (Ta = 25°C)

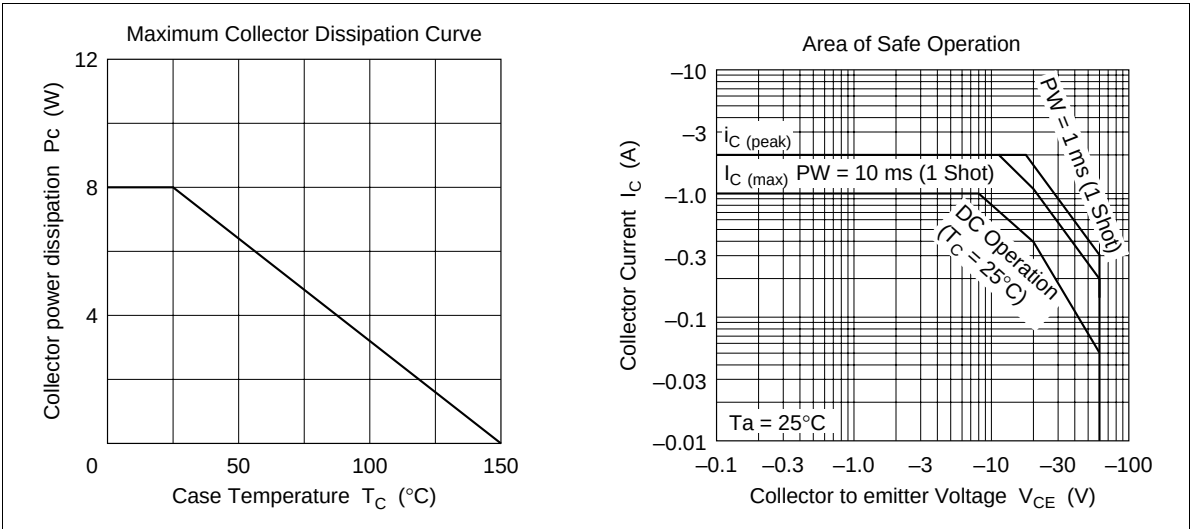
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-60	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-1	A
Collector peak current	$I_{C(peak)}$	-2	A
Collector power dissipation	P_C	1	W
	P_C^{*1}	8	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

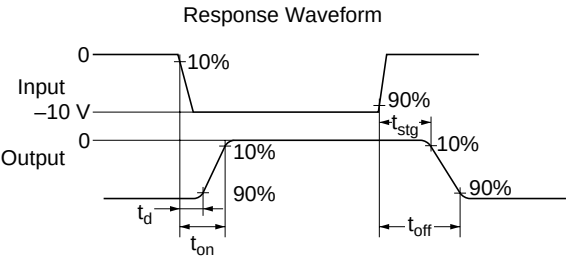
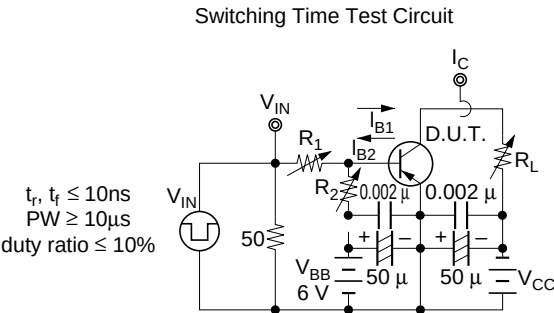
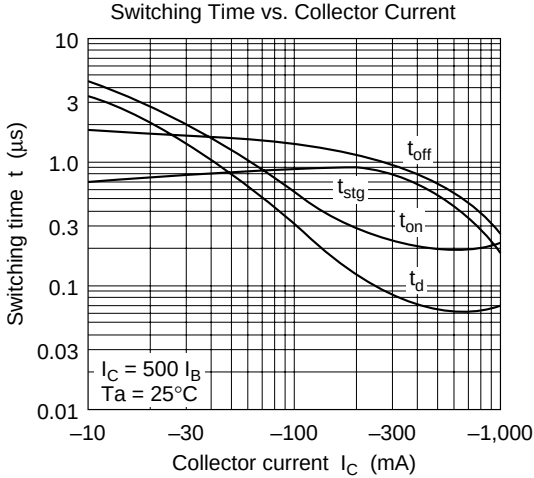
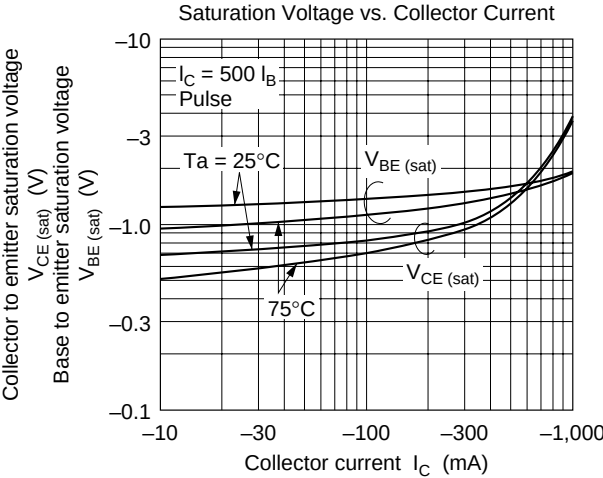
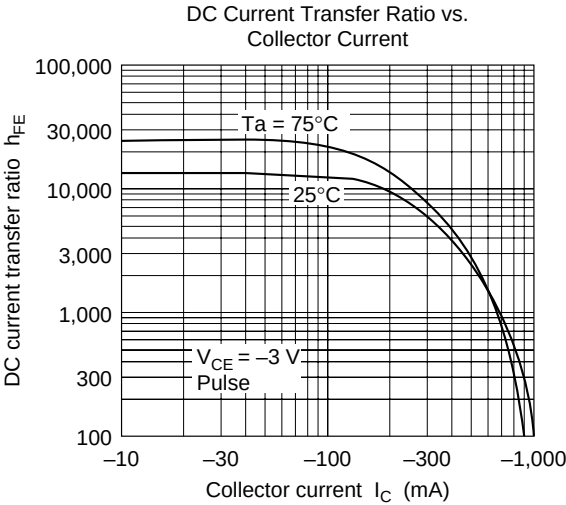
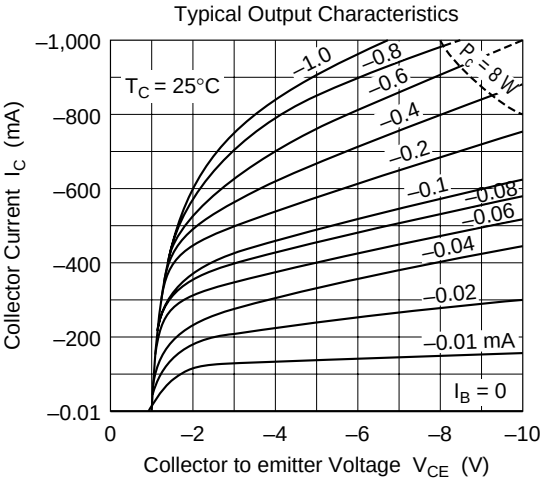
Note: 1. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -1\text{ mA}$, $R_{BE} = \infty$
Collector cutoff current	I_{CBO}	—	—	-1.0	μA	$V_{CB} = -60\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-1.0	μA	$V_{EB} = -7\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	1000	—	—		$V_{CE} = -3\text{ V}$, $I_C = -500\text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-2.0	V	$I_C = -500\text{ mA}$, $I_B = -1\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-2.0	V	
Turn on time	t_{on}	—	0.7	—	μs	$I_C = -500\text{ mA}$
Turn off time	t_{off}	—	0.8	—	μs	$I_{B1} = -I_{B2} = -1\text{ mA}$

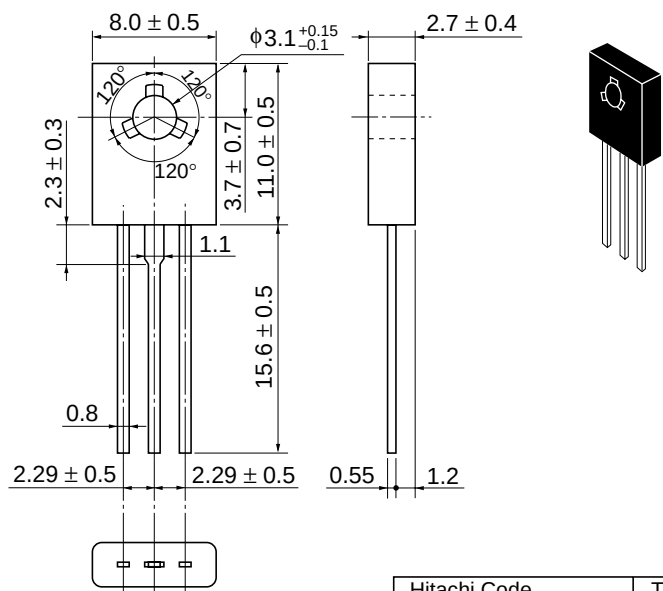
Note: 1. Pulse test





Package Dimensions

Unit: mm



Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Mass (reference value)	0.67 g

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